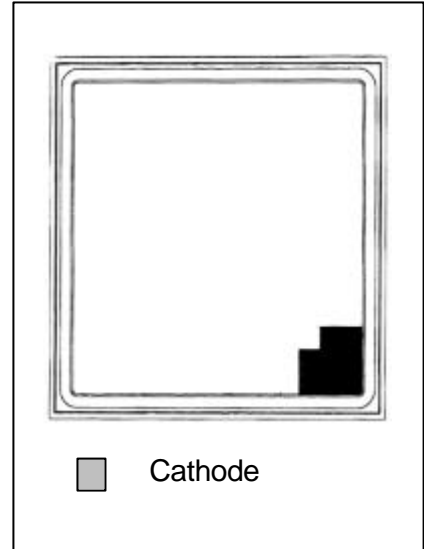


QSD-2160NA

SILICON PIN PHOTODIODE

COMMON ANODE TYPE PIN PHOTO DIODE.
HIGH SPEED SENSITIVITY.

- **DIE SIZE** 1.60mm × 1.60mm
- **DIE THICKNESS** 400 ± 15μm
- **METALLIZATION**
 - TOP Al
 - BOTTOM Au
- **BONDING PAD SIZE**
 - CATHODE (TOP) 300μm × 300μm
 - ANODE (BOTTOM)



- **ABSOLUTE MAXIMUM RATINGS (Ta= 25° C)**

Parameter	Symbol	Maximum rating	Unit
Reverse Breakdown Voltage	B_{VR}	-35	V
Junction Temperature	T_J	150	°C

- **ELECTRICAL / OPTICAL CHARACTERISTICS (Ta= 25° C)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Open Circuit Voltage	V_{OP}	Note(1)	-0.3	-0.32		V
Short Circuit Current	I_{SC}	Note(1)	-16	-20		μA
Spectrum Sensitivity	λ		430 ~ 1,090			nm
Peak Sensing Wavelength	λ_P			880		nm
Forward Voltage	V_F	$I_F=100\text{ mA}$		-1.3	-1.5	V
Dark Current	I_D	$V_R=10\text{V}$		-5	-10	nA
Reverse Breakdown Voltage	B_{VR}	$I_R=10\mu\text{A}$	-50	-70		V

Note(1): Parallel light of 1,000 Lux illumination is applied by a Tungsten lamp of 2856k.